POLITÉCNICA

"Ingeniamos el futuro"

Departamento de Ingeniería Electrónica

Inversor CMOS

Créditos de las transparencias:

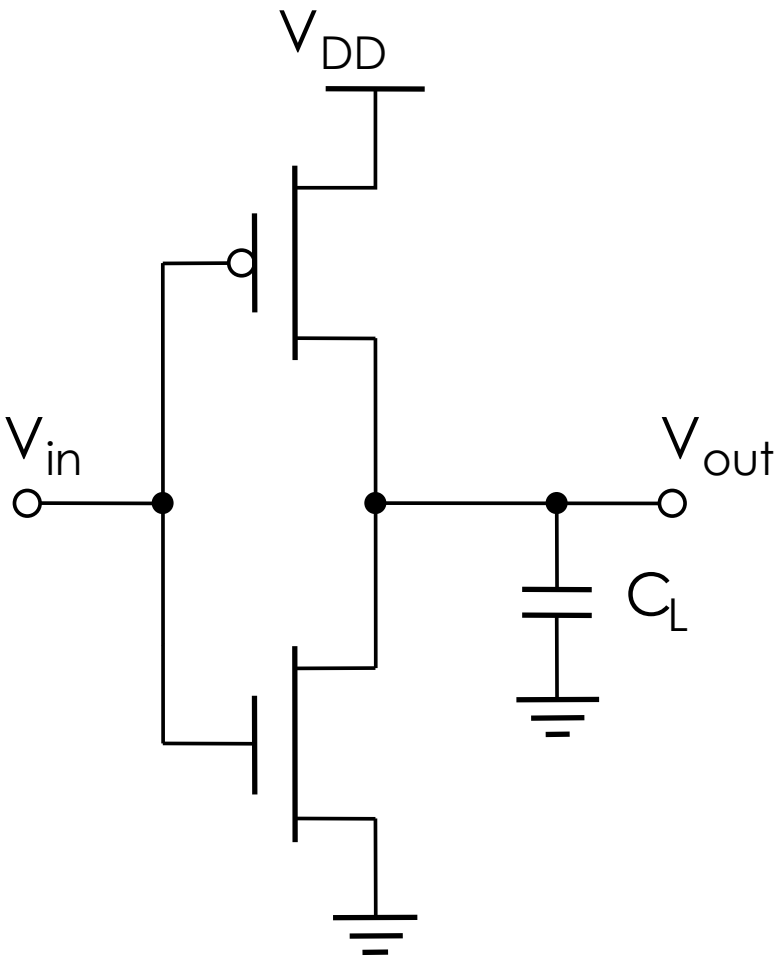
- Digital Integrated Circuits. Second Edition. Jan M. Rabaey, Anantha Chandrakasan, and Borivoje Nikolic
- Asignatura de David Harris en el Harvey Mudd College
- EGE535 Low Power VLSI Design, Damu Radhakrishnan, State University of New York
- Elaboración Propia

Clase de hoy

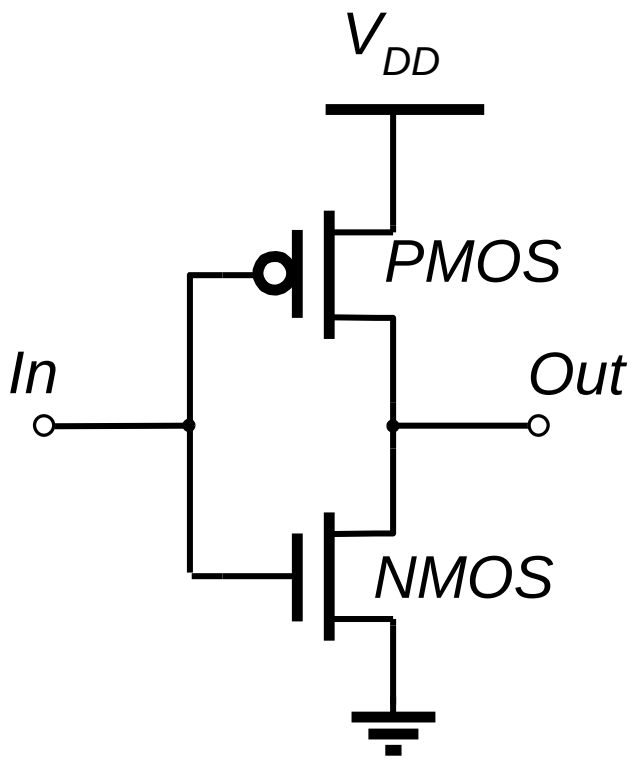
- Inversor CMOS
  - Comportamiento en estática
  - Métricas de calidad
  - Comportamiento en dinámica
  - Otros estilos lógicos

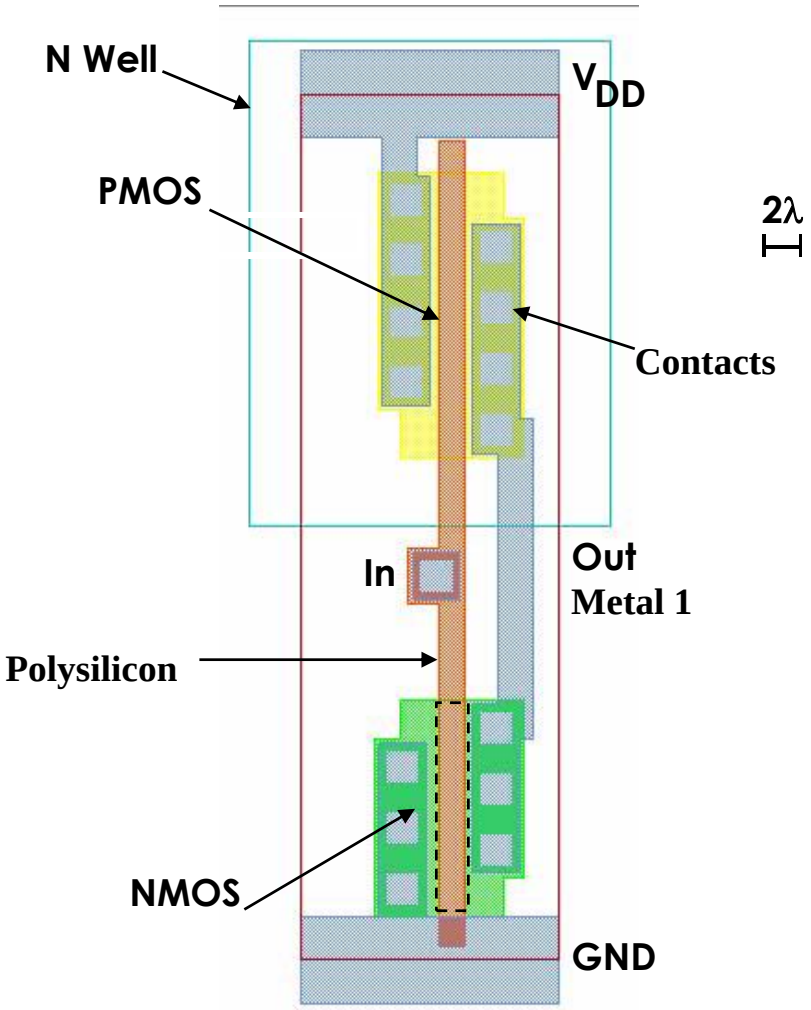
Bibliografía:
Capítulo 2 Weste-Eshraghian
Capítulo 5 Rabaey

The CMOS Inverter: A First Glance



CMOS Inverter

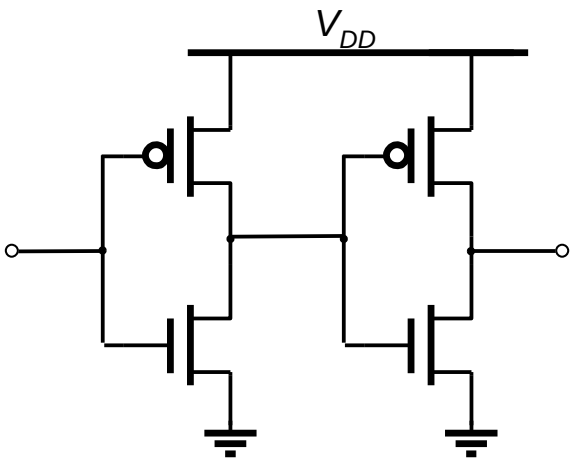


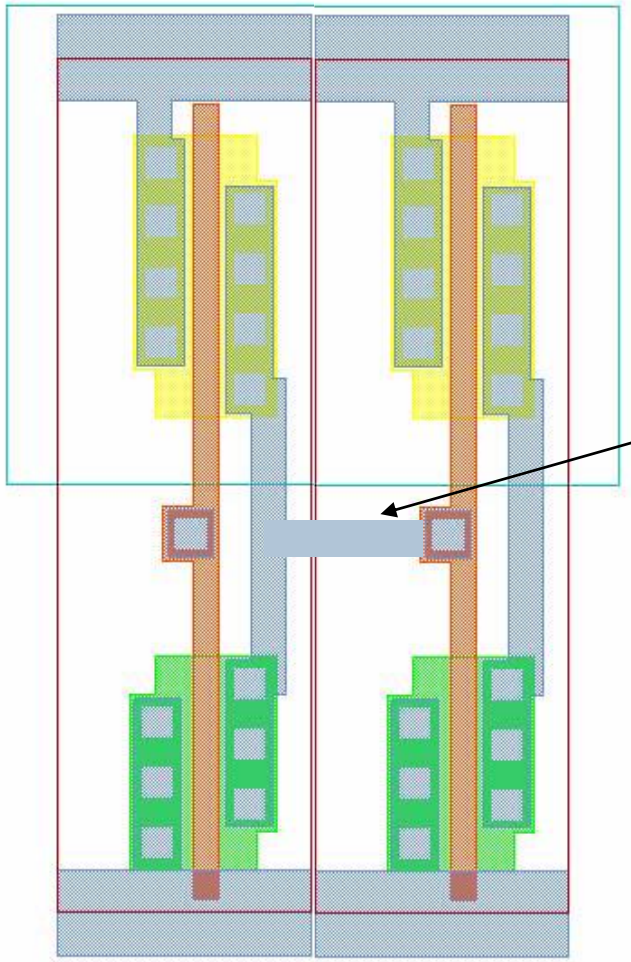


Two Inverters

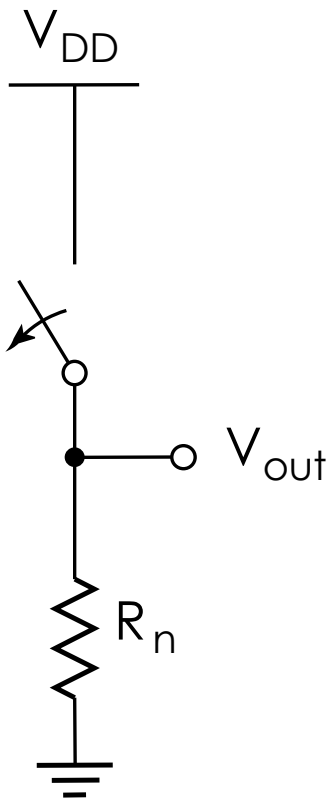
Share power and ground

Abut cells

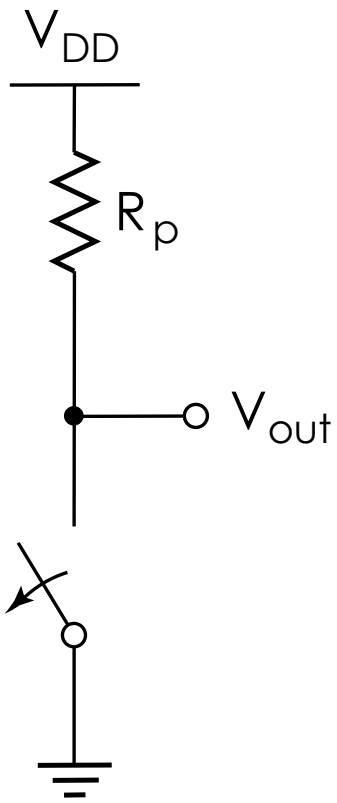




CMOS Inverter
First-Order DC Analysis



$V_{in} = V_{DD}$



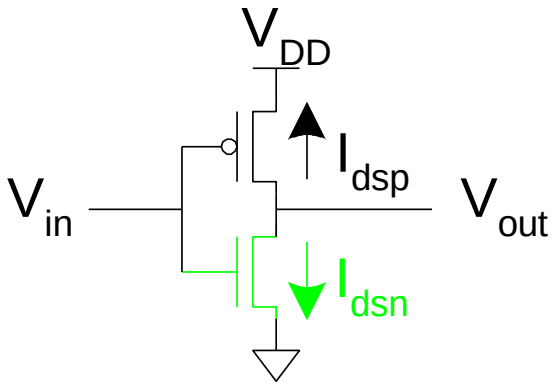
$V_{in} = 0$

Transistor Operation

- Current depends on region of transistor behavior
- For what V_{in} and V_{out} are nMOS and pMOS in
  - Cutoff?
  - Linear?
  - Saturation?

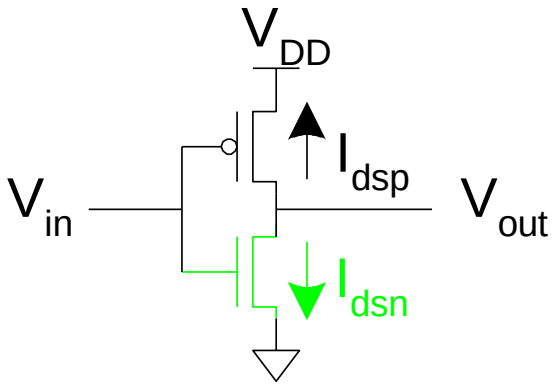
nMOS Operation

Cutoff	Linear	Saturated
V_{gsn} <	V_{gsn} >	V_{gsn} >
	V_{dsn} <	V_{dsn} >



nMOS Operation

Cutoff	Linear	Saturated
$V_{gsn} < V_{tn}$	$V_{gsn} > V_{tn}$ $V_{dsn} < V_{gsn} - V_{tn}$	$V_{gsn} > V_{tn}$ $V_{dsn} > V_{gsn} - V_{tn}$

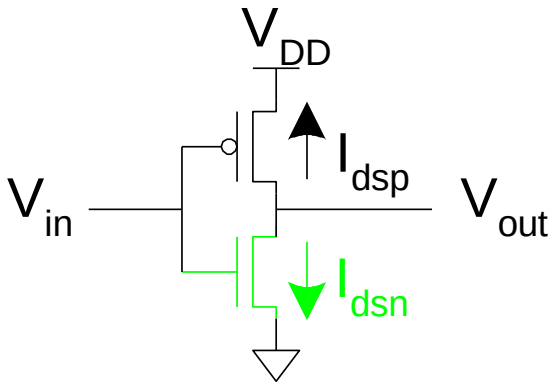


nMOS Operation

Cutoff	Linear	Saturated
$V_{gsn} < V_{tn}$	$V_{gsn} > V_{tn}$ $V_{dsn} < V_{gsn} - V_{tn}$	$V_{gsn} > V_{tn}$ $V_{dsn} > V_{gsn} - V_{tn}$

$V_{gsn} = V_{in}$

$V_{dsn} = V_{out}$

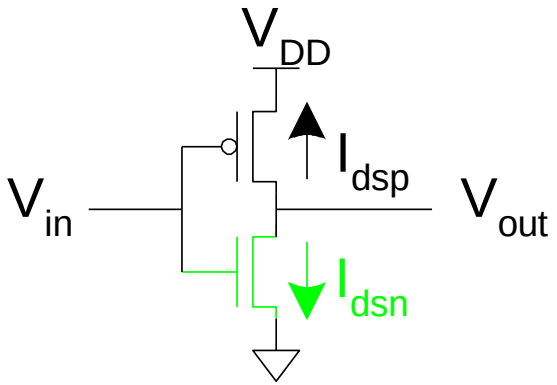


nMOS Operation

Cutoff	Linear	Saturated
$V_{gsn} < V_{tn}$ $V_{in} < V_{tn}$	$V_{gsn} > V_{tn}$ $V_{in} > V_{tn}$ $V_{dsn} < V_{gsn} - V_{tn}$ $V_{out} < V_{in} - V_{tn}$	$V_{gsn} > V_{tn}$ $V_{in} > V_{tn}$ $V_{dsn} > V_{gsn} - V_{tn}$ $V_{out} > V_{in} - V_{tn}$

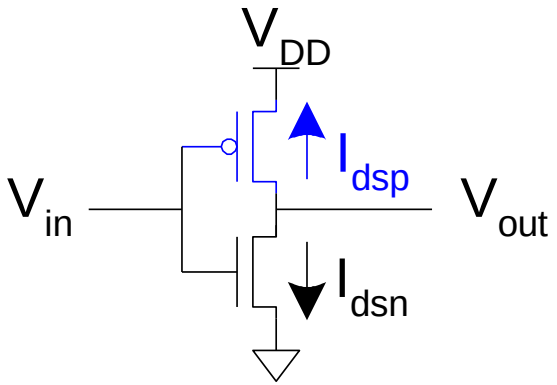
$V_{gsn} = V_{in}$

$V_{dsn} = V_{out}$



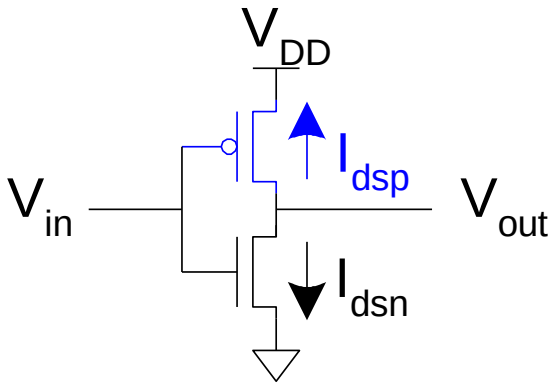
pMOS Operation

Cutoff	Linear	Saturated
$V_{gsp} >$	$V_{gsp} <$ $V_{dsp} >$	$V_{gsp} <$ $V_{dsp} <$



pMOS Operation

Cutoff	Linear	Saturated
$V_{gsp} > V_{tp}$	$V_{gsp} < V_{tp}$ $V_{dsp} > V_{gsp} - V_{tp}$	$V_{gsp} < V_{tp}$ $V_{dsp} < V_{gsp} - V_{tp}$



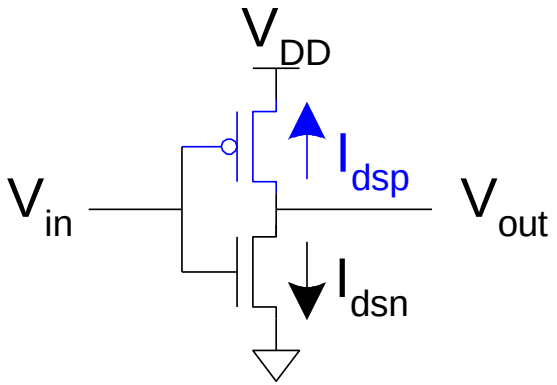
pMOS Operation

Cutoff	Linear	Saturated
$V_{gsp} > V_{tp}$	$V_{gsp} < V_{tp}$ $V_{dsp} > V_{gsp} - V_{tp}$	$V_{gsp} < V_{tp}$ $V_{dsp} < V_{gsp} - V_{tp}$

$V_{gsp} = V_{in} - V_{DD}$

$V_{dsp} = V_{out} - V_{DD}$

$V_{tp} < 0$



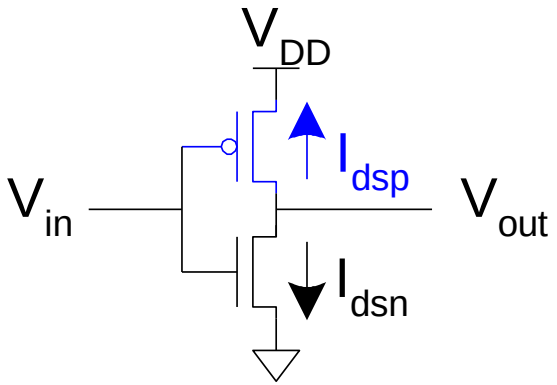
pMOS Operation

Cutoff	Linear	Saturated
$V_{gsp} > V_{tp}$ $V_{in} > V_{DD} + V_{tp}$	$V_{gsp} < V_{tp}$ $V_{in} < V_{DD} + V_{tp}$ $V_{dsp} > V_{gsp} - V_{tp}$ $V_{out} > V_{in} - V_{tp}$	$V_{gsp} < V_{tp}$ $V_{in} < V_{DD} + V_{tp}$ $V_{dsp} < V_{gsp} - V_{tp}$ $V_{out} < V_{in} - V_{tp}$

$V_{gsp} = V_{in} - V_{DD}$

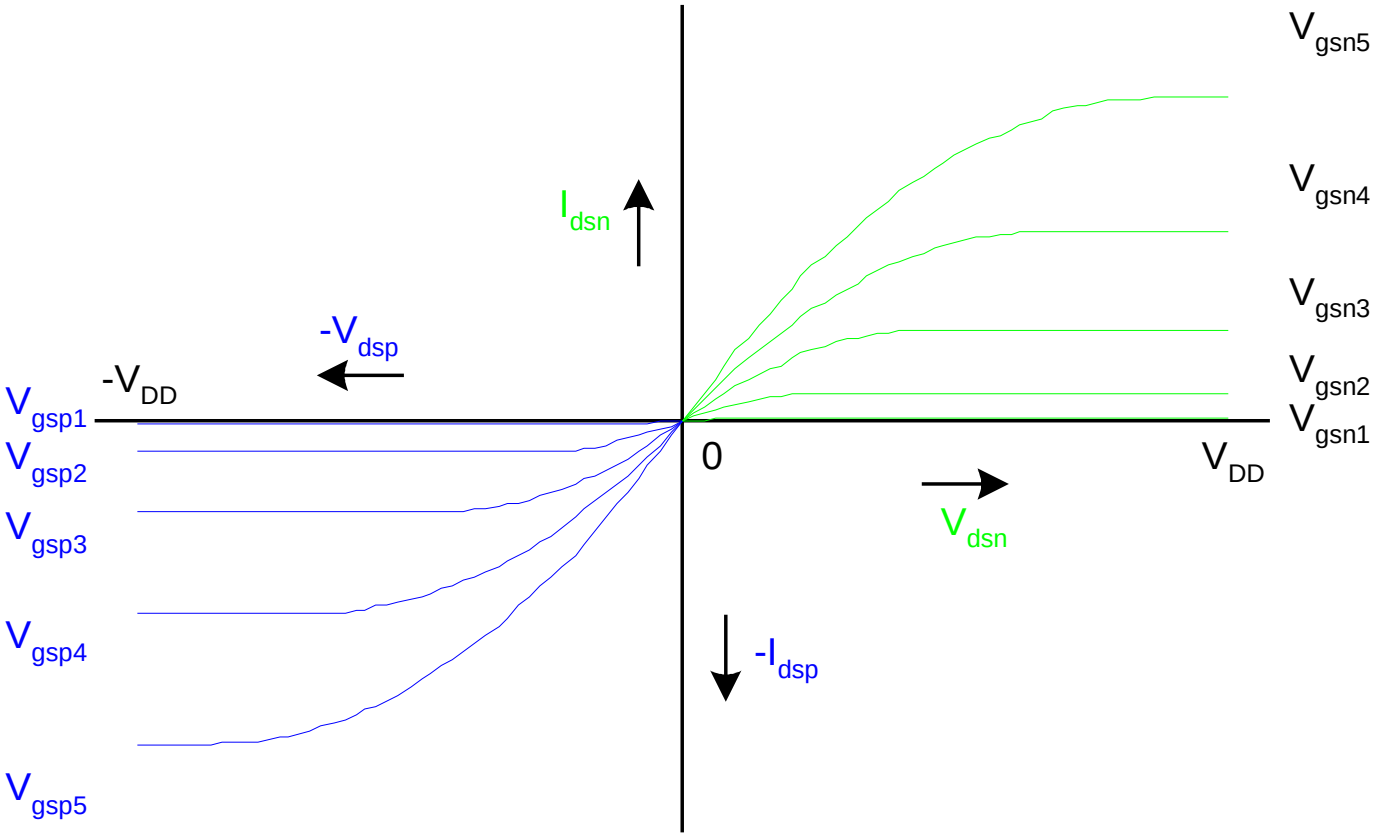
$V_{dsp} = V_{out} - V_{DD}$

$V_{tp} < 0$

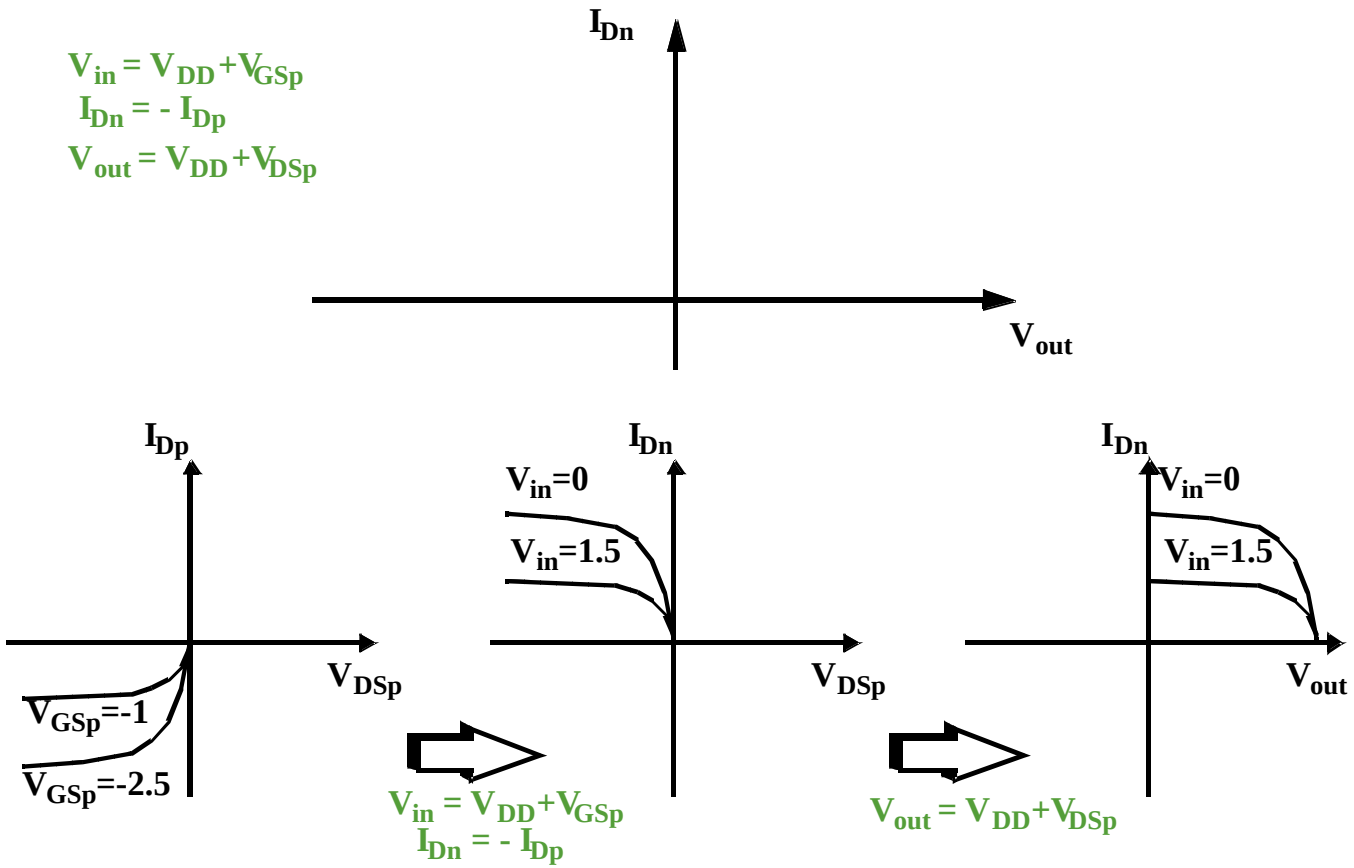


I-V Characteristics

- Make pMOS is wider than nMOS such that $\beta_n = \beta_p$

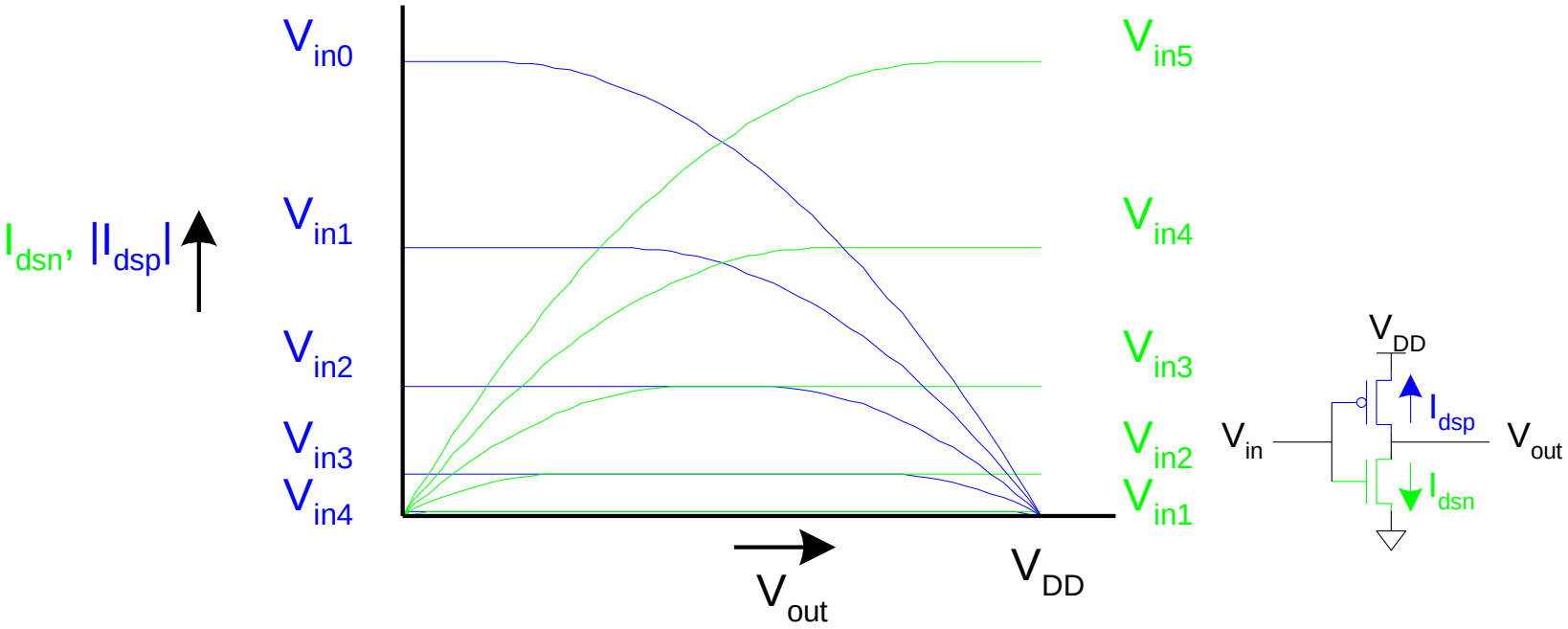


PMOS Load Lines



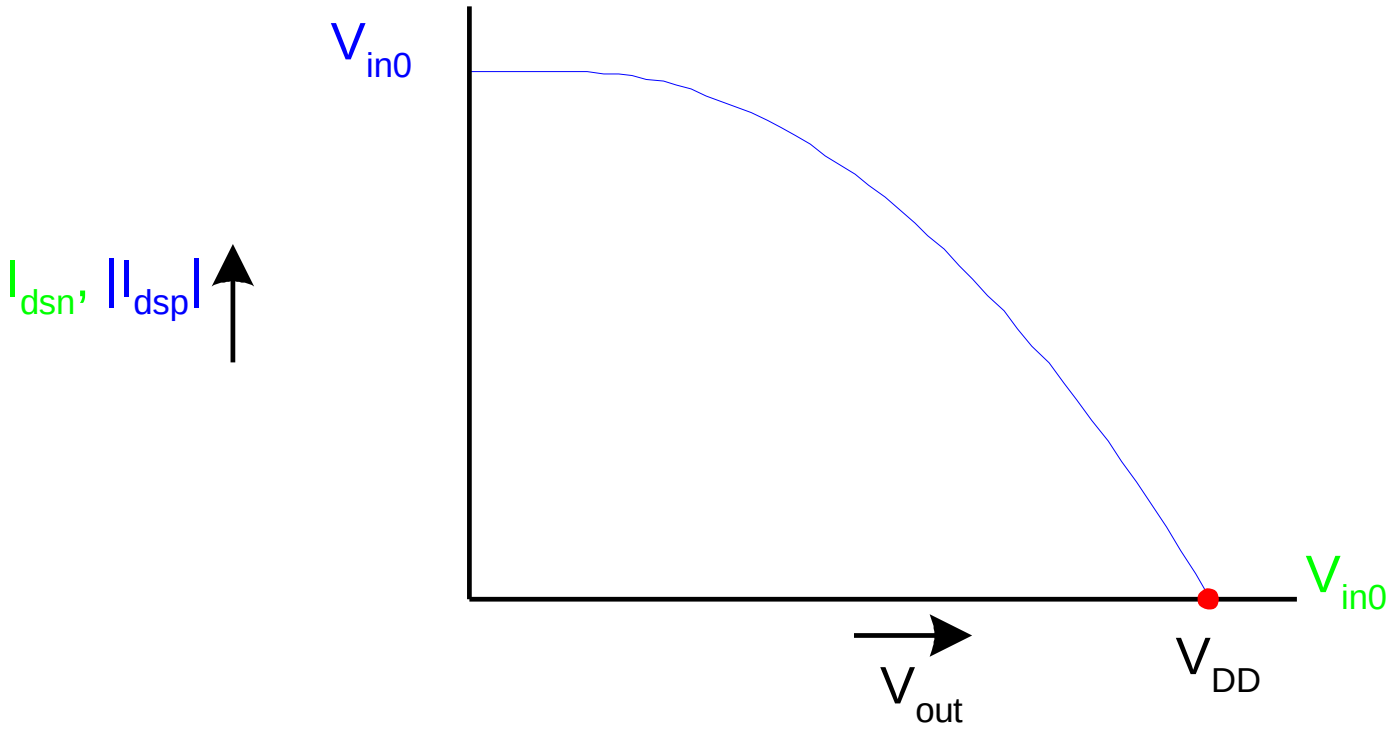
Load Line Analysis

- For a given V_{in}:
  - Plot I_{dsn}, I_{dsp} vs. V_{out}
  - V_{out} must be where |currents| are equal in



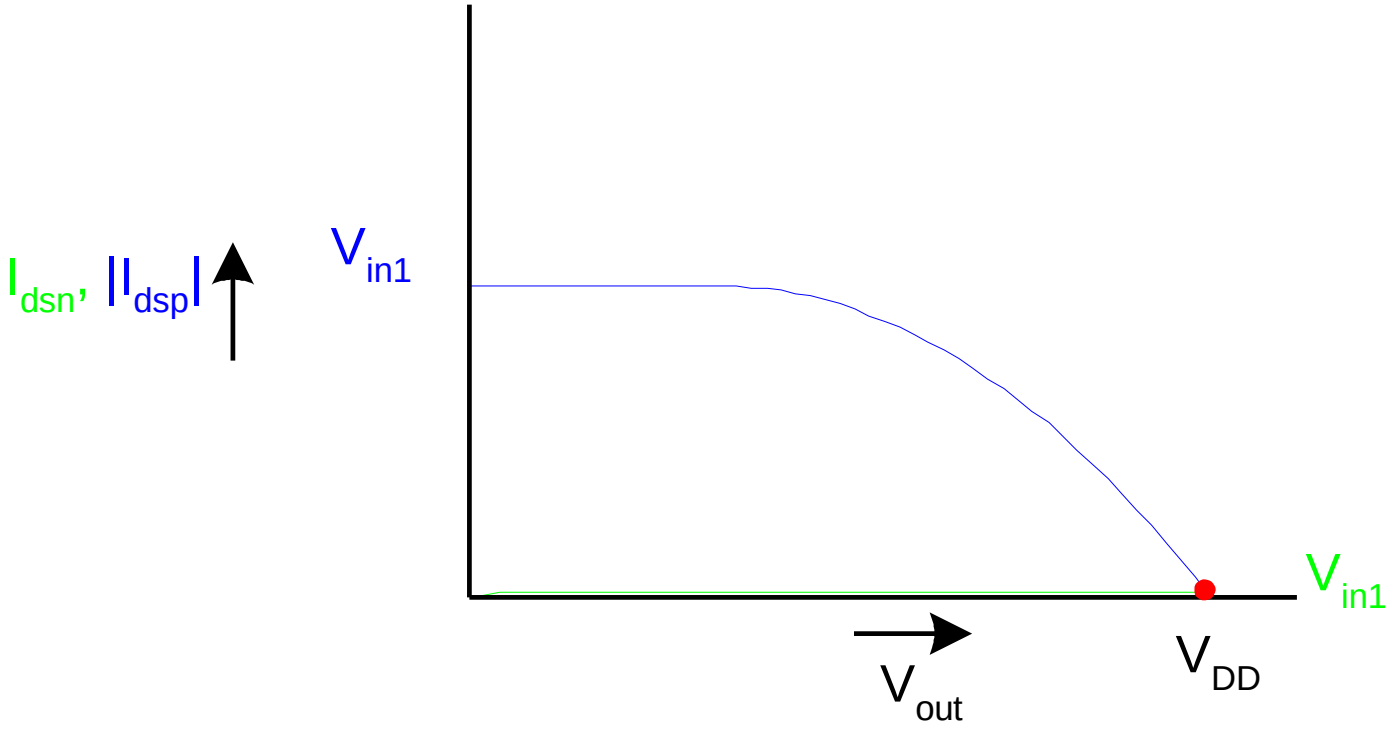
Load Line Analysis

- $V_{in} = 0$
- Transistor n is off



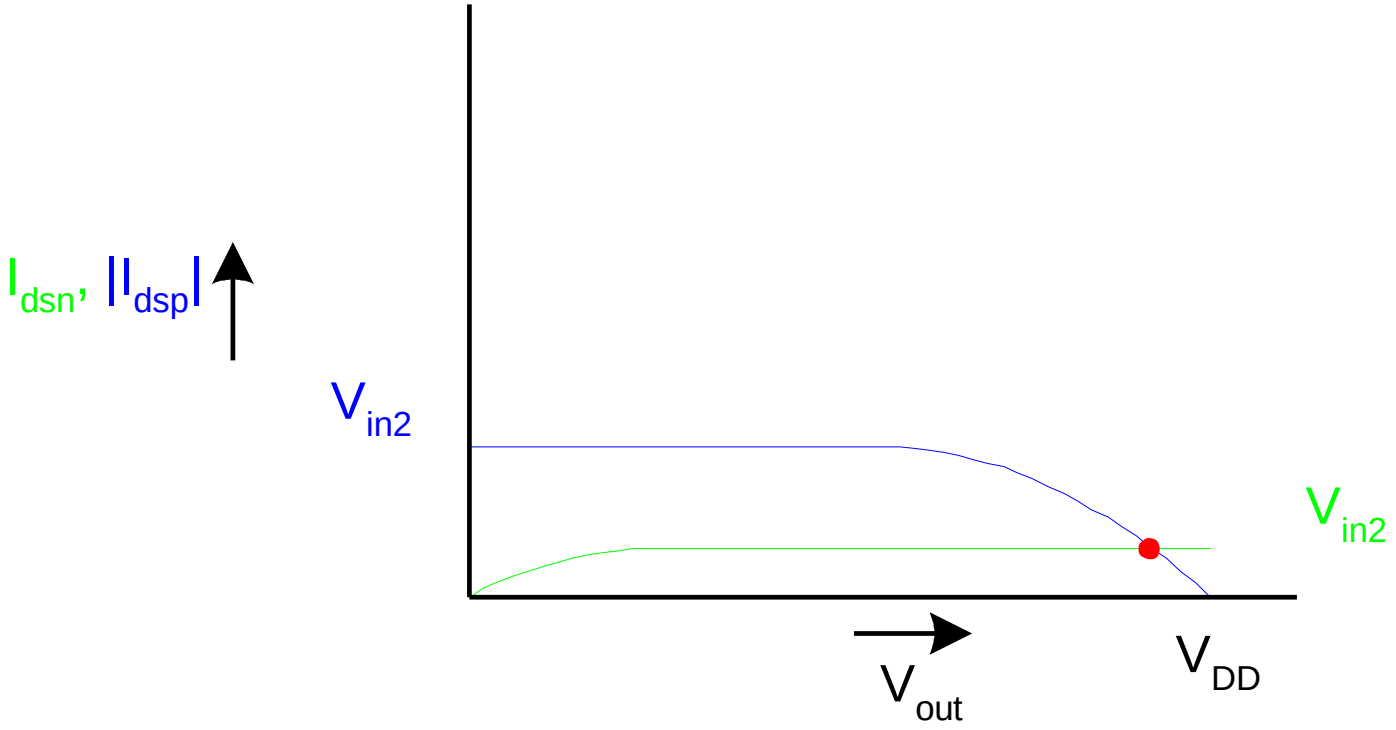
Load Line Analysis

- $V_{in} = 0.2V_{DD}$



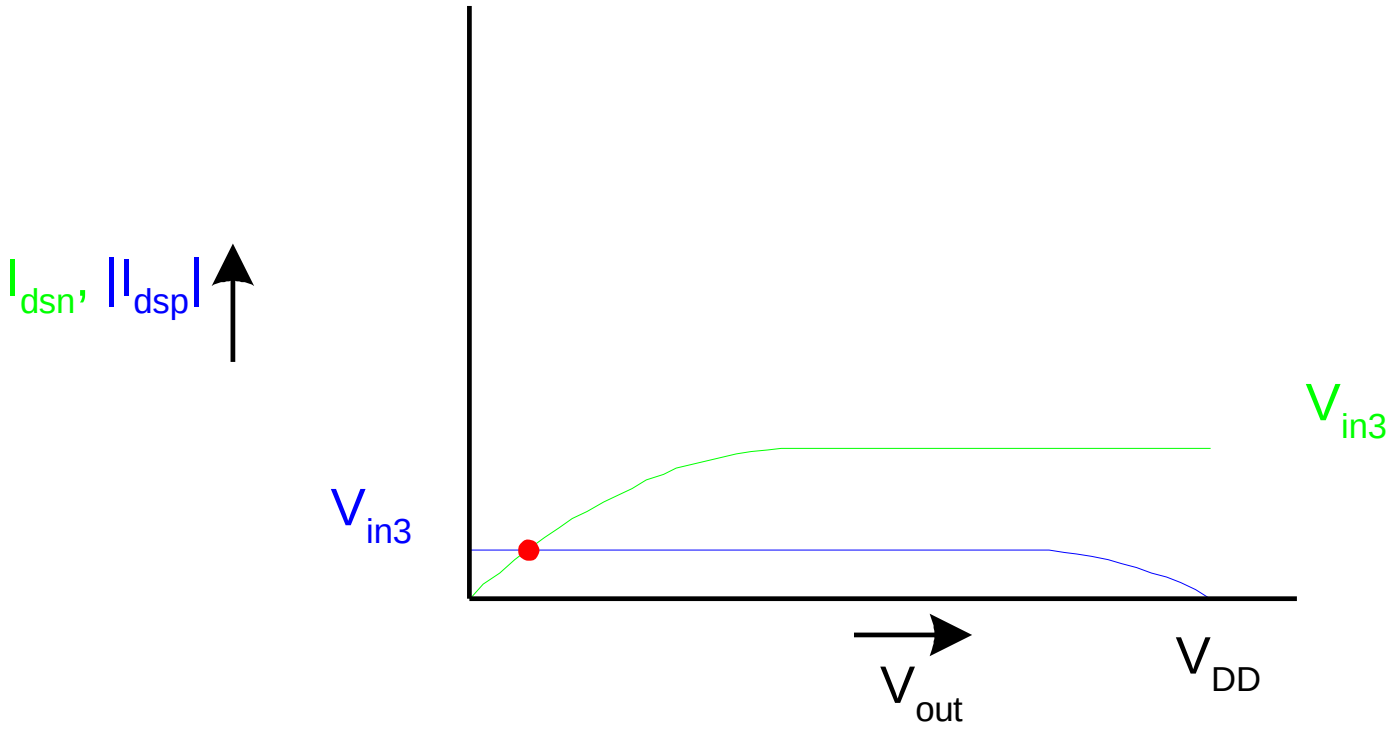
Load Line Analysis

- $V_{in} = 0.4V_{DD}$



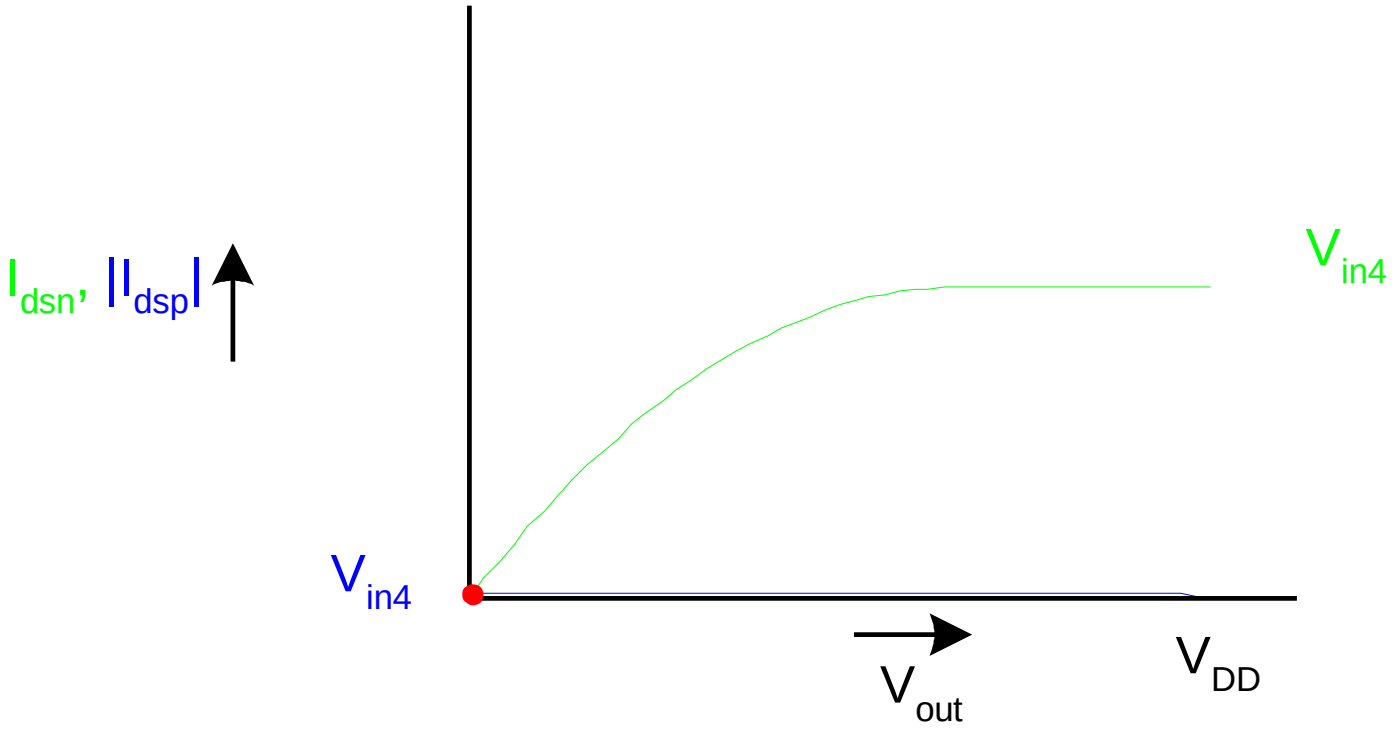
Load Line Analysis

- $V_{in} = 0.6V_{DD}$



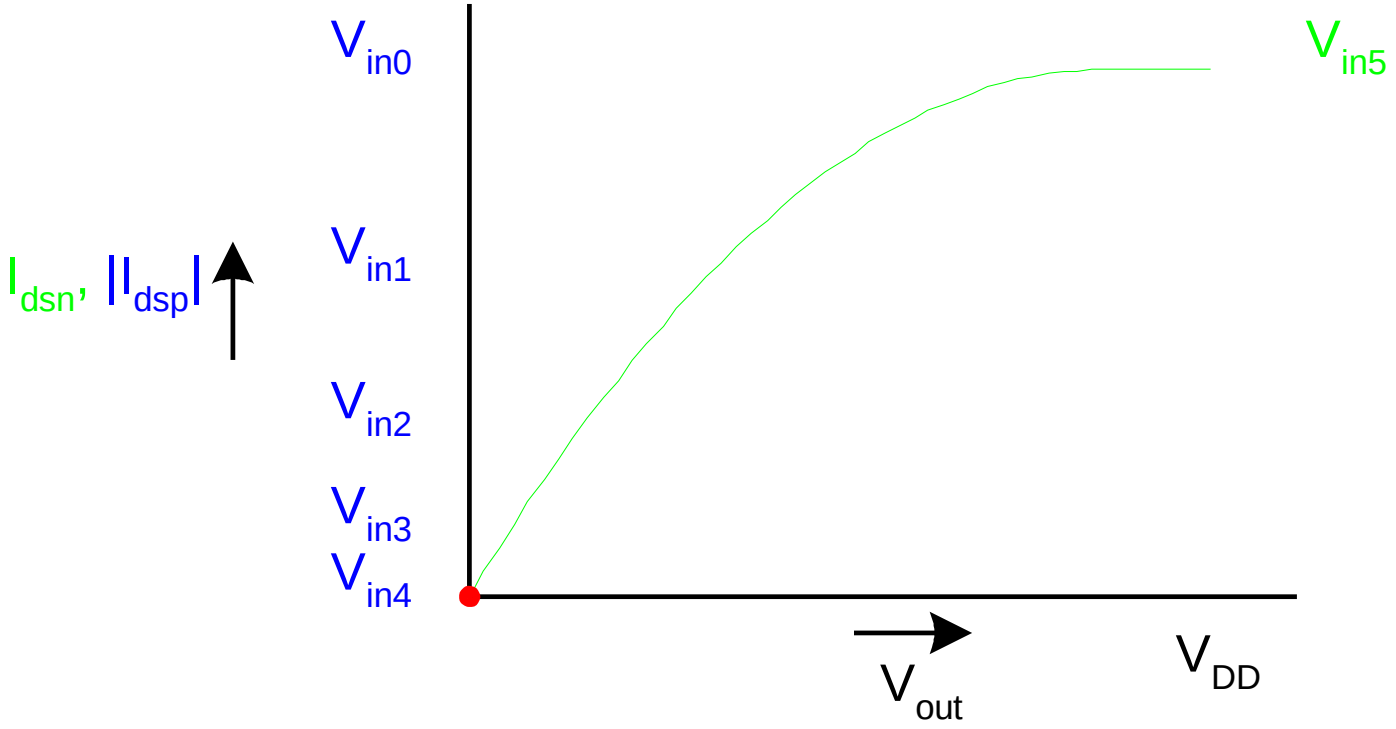
Load Line Analysis

- $V_{in} = 0.8V_{DD}$

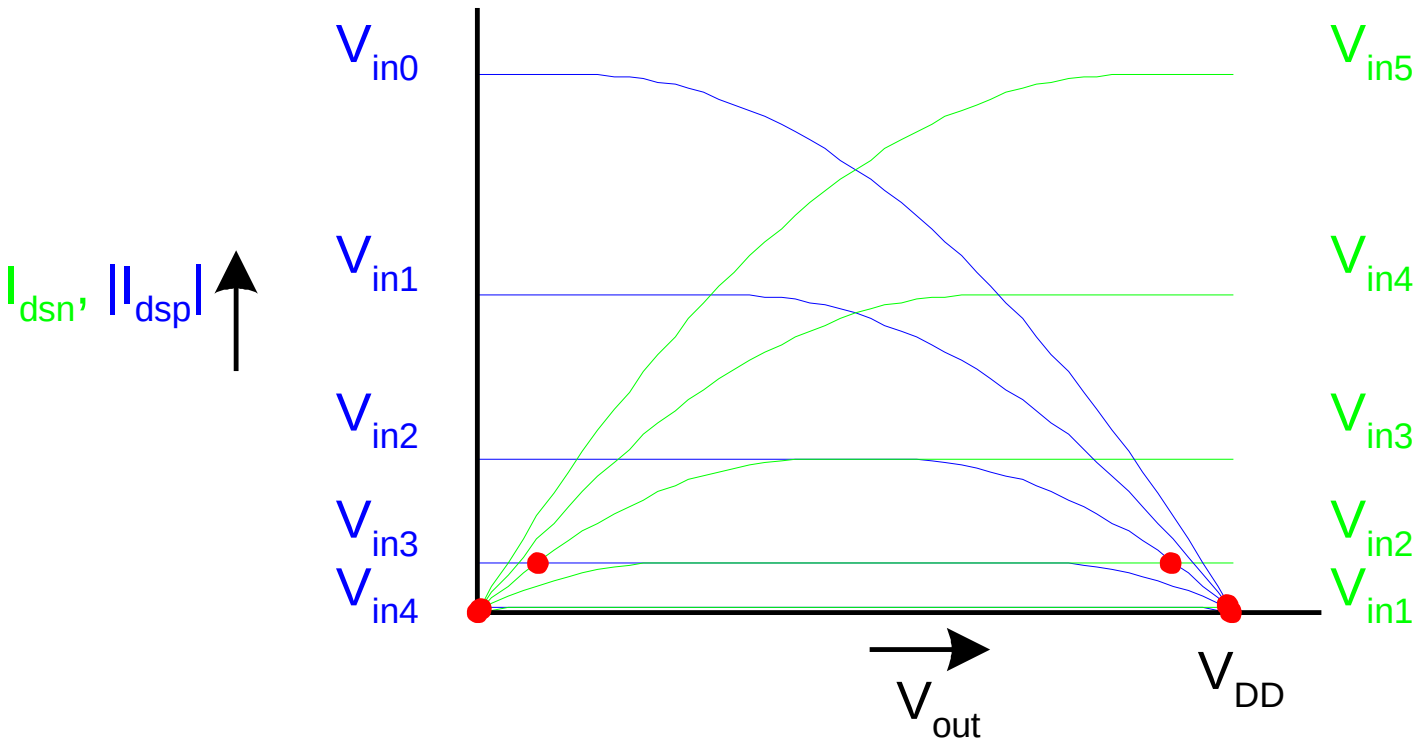


Load Line Analysis

- $V_{in} = V_{DD}$
- Trasistor p is off

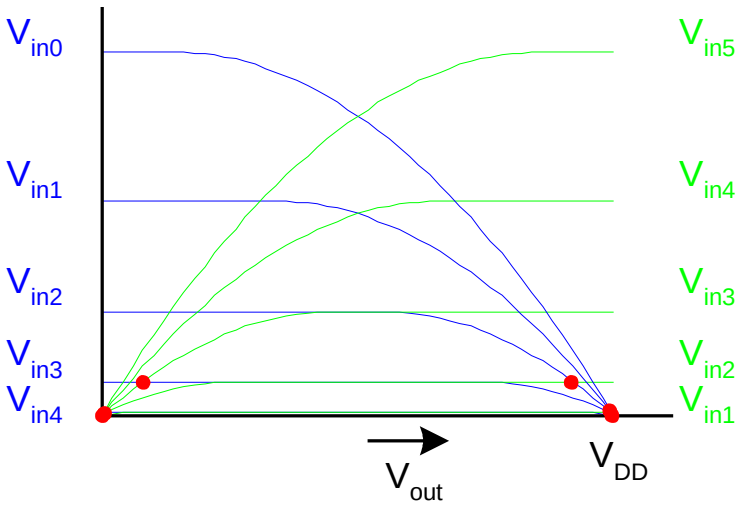


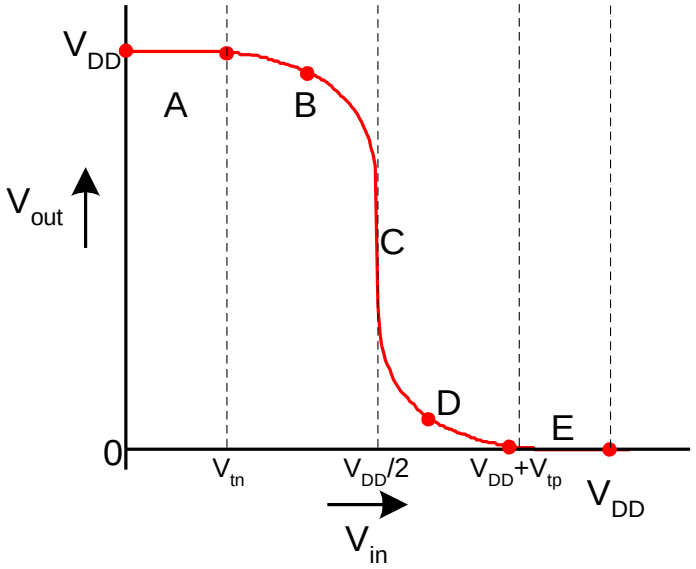
Load Line Summary



DC Transfer Curve

- Transcribe points onto V_{in} vs. V_{out} plot

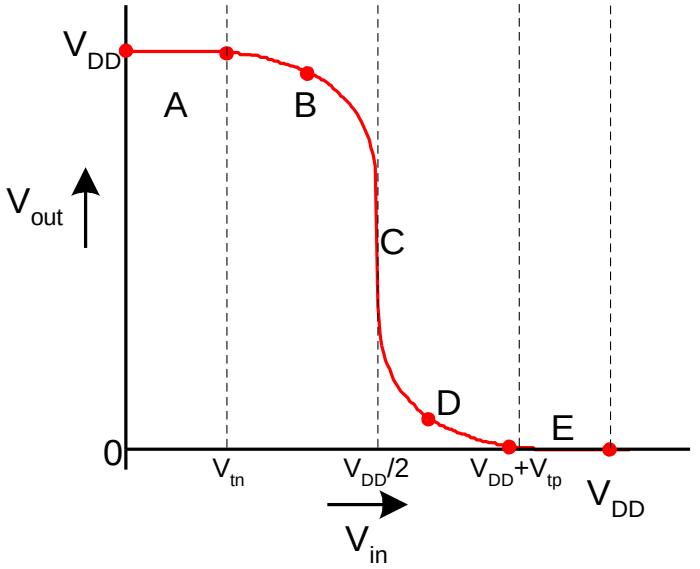




Operating Regions

- Revisit transistor operating regions

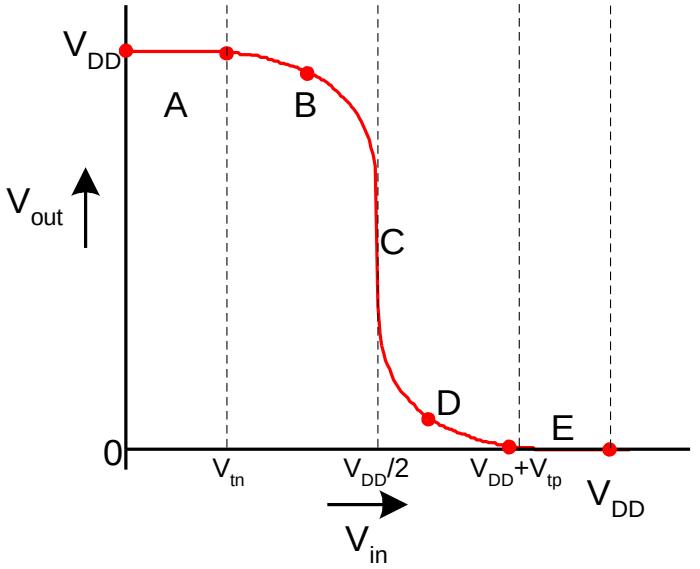
Region	nMOS	pMOS
A		
B		
C		
D		
E		



Operating Regions

- Revisit transistor operating regions

Region	nMOS	pMOS
A	Cutoff	Linear
B	Saturation	Linear
C	Saturation	Saturation
D	Linear	Saturation
E	Linear	Cutoff



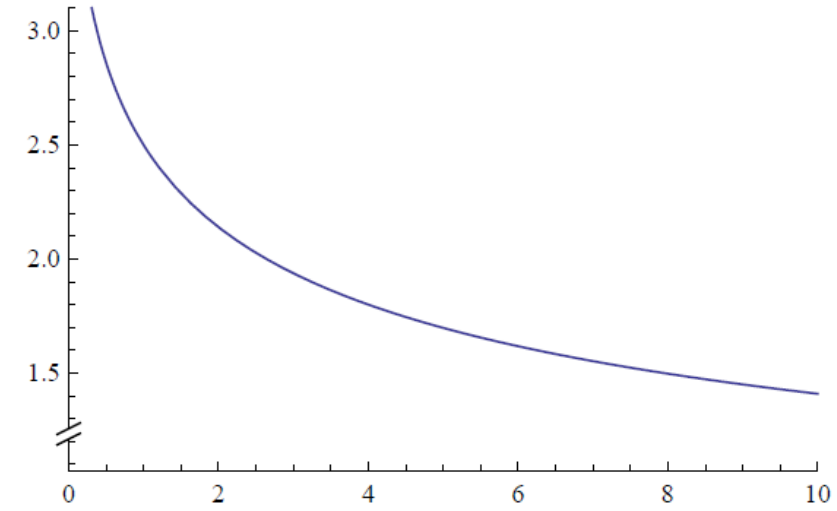
Dependencia del umbral con la relación de aspecto

Plot[(4.6 + 0.4 Sqrt[y])/(1 + Sqrt[y]), {y, 0, 10}]

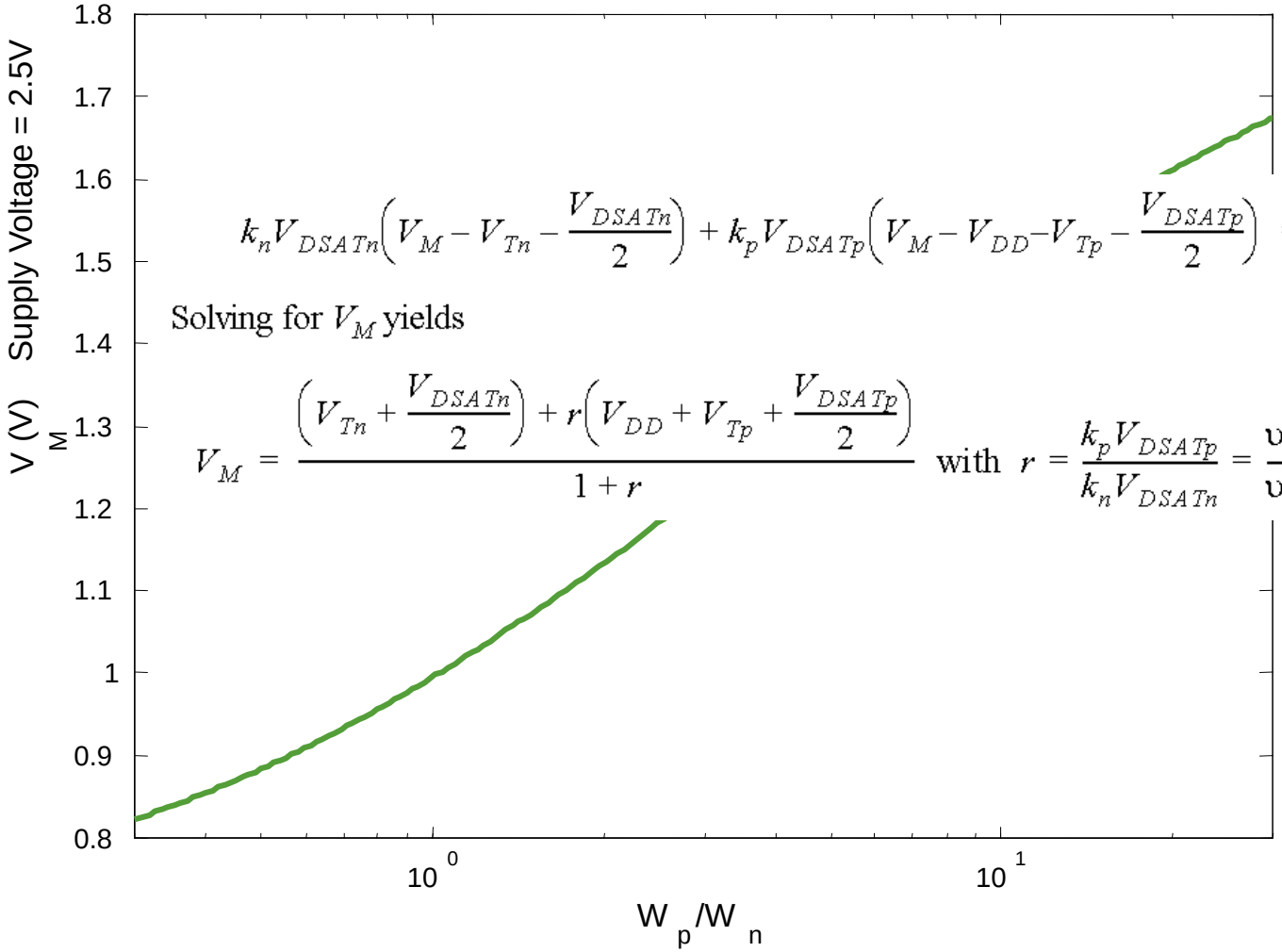
Input interpretation:

plot	$\frac{4.6 + 0.4\sqrt{y}}{1 + \sqrt{y}}$	$y = 0$ to 10

Plot:



Switching Threshold as a function of Transistor Ratio



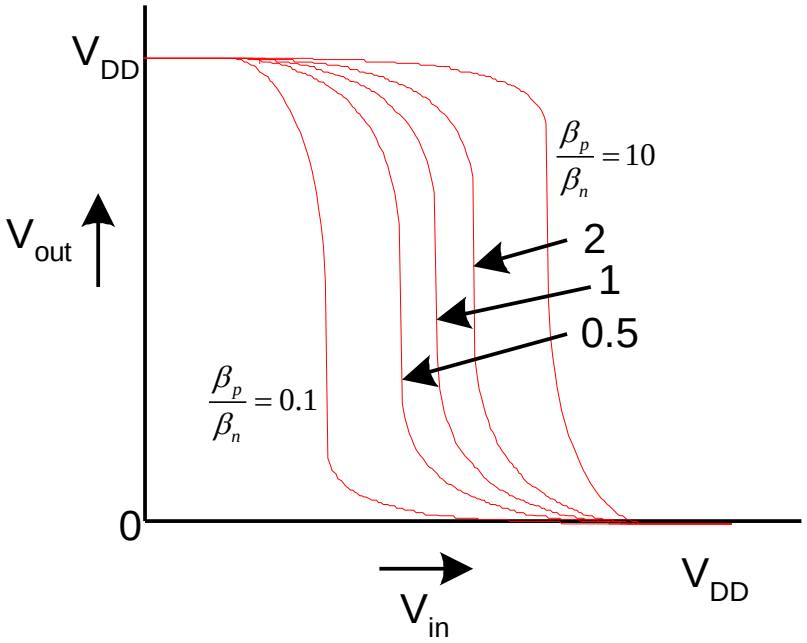
$$k_n V_{DSATn}\left(V_M - V_{Tn} - \frac{V_{DSATn}}{2}\right) + k_p V_{DSATp}\left(V_M - V_{DD} - V_{Tp} - \frac{V_{DSATp}}{2}\right) = 0$$

Solving for V_M yields

$$V_M = \frac{\left(V_{Tn} + \frac{V_{DSATn}}{2}\right) + r\left(V_{DD} + V_{Tp} + \frac{V_{DSATp}}{2}\right)}{1 + r} \quad \text{with} \quad r = \frac{k_p V_{DSATp}}{k_n V_{DSATn}} = \frac{\upsilon_{satp} W_p}{\upsilon_{satn} W_n}$$

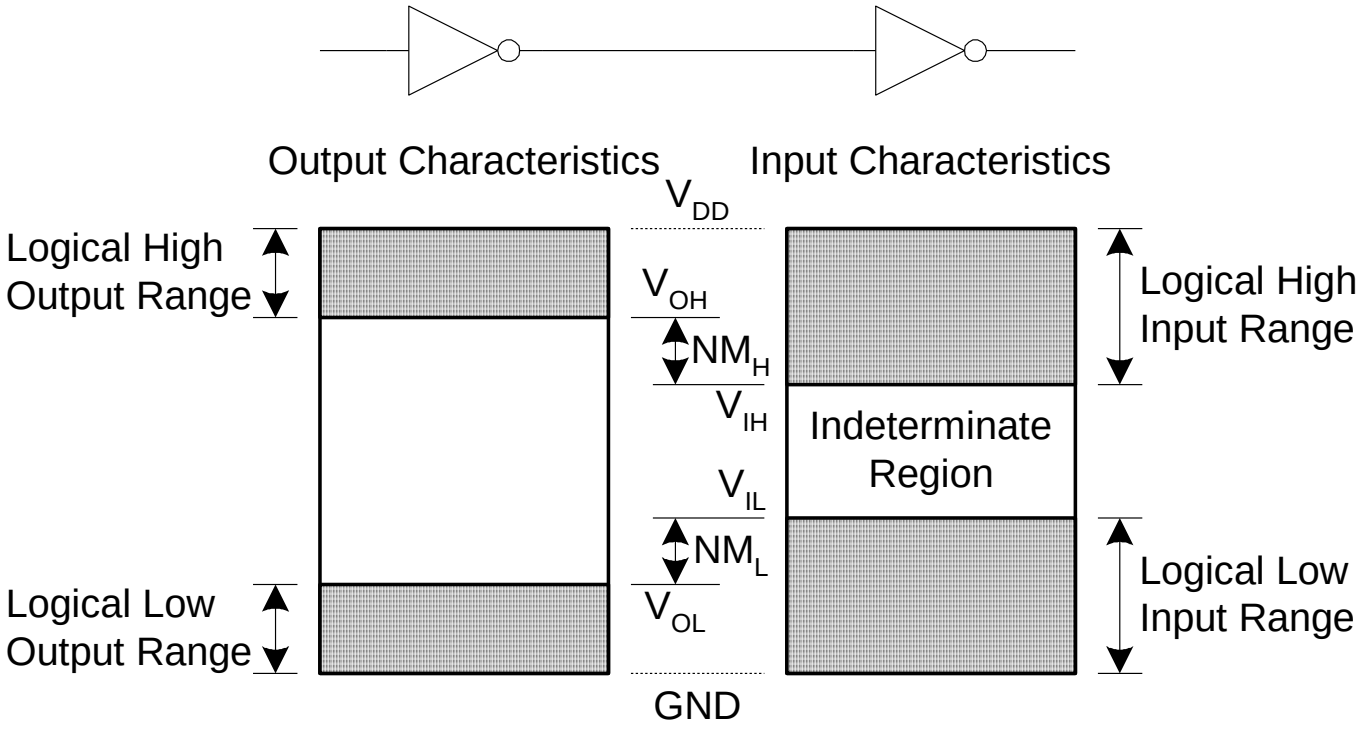
Beta Ratio

- If $\beta_p / \beta_n \neq 1$, switching point will move from $V_{DD}/2$
- Called *skewed* gate
- Other gates: collapse into equivalent inverter



Noise Margins

- How much noise can a gate input see before it does not recognize the input?

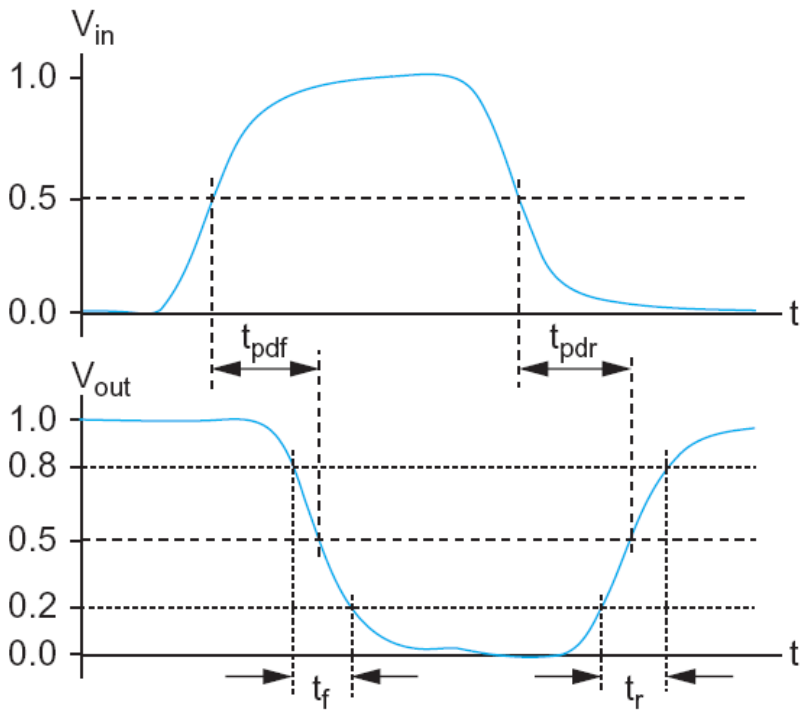


Transient Response

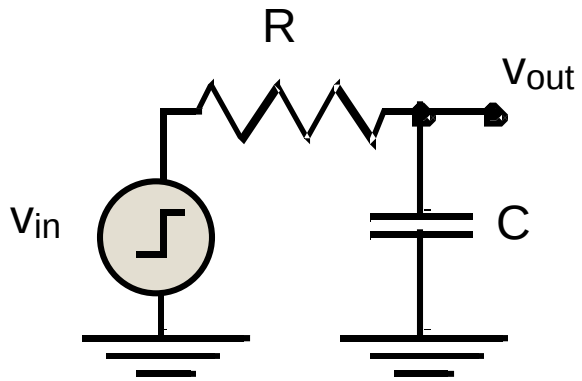
- *DC analysis* tells us V_{out} if V_{in} is constant
- *Transient analysis* tells us $V_{out}(t)$ if $V_{in}(t)$ changes
  - Requires solving differential equations
- Input is usually considered to be a step or ramp
  - From 0 to V_{DD} or vice versa

Delay Definitions

- $\mathbf{t_{pdr}}$: *rising propagation delay*
  - From input to rising output crossing $V_{DD}/2$
- $\mathbf{t_{pdf}}$: *falling propagation delay*
  - From input to falling output crossing $V_{DD}/2$
- $\mathbf{t_{pd}}$: *average propagation delay*
  - $t_{pd} = (t_{pdr} + t_{pdf})/2$
- $\mathbf{t_r}$: *rise time*
  - From output crossing 0.2 V_{DD} to 0.8 V_{DD}
- $\mathbf{t_f}$: *fall time*
  - From output crossing 0.8 V_{DD} to 0.2 V_{DD}



A First-Order RC Network



$$V(t) = \frac{Q(t)}{C} = \frac{1}{C}\int_{t_0}^{t} I(\tau)\mathrm{d}\tau + V(t_0)$$

$$I(t) = \frac{\mathrm{d}Q(t)}{\mathrm{d}t} = C\frac{\mathrm{d}V(t)}{\mathrm{d}t}$$

$$v_{out}(t) = (1 - e^{-t/\tau})\ V$$

$t_p = \ln(2)\ \tau = 0.69\ RC$

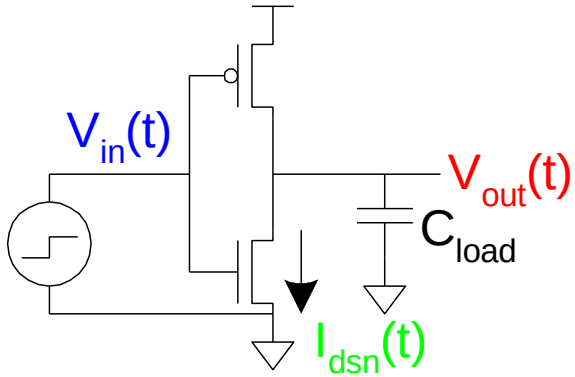
Inverter Step Response

- Ex: find step response of inverter driving load cap

$$V_{in}(t) =$$

$$V_{out}(t < t_0) =$$

$$\frac{dV_{out}(t)}{dt} =$$



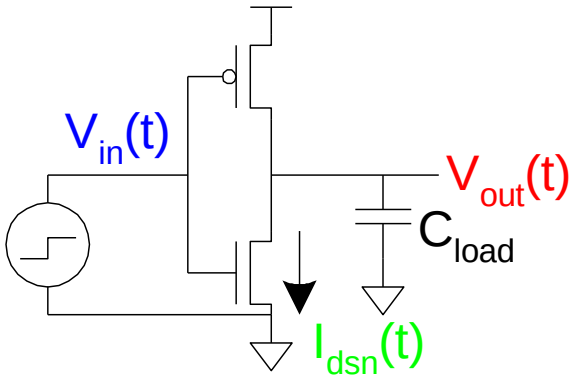
Inverter Step Response

- Ex: find step response of inverter driving load cap

$$V_{in}(t) = u(t - t_0)V_{DD}$$

$$V_{out}(t < t_0) =$$

$$\frac{dV_{out}(t)}{dt} =$$



Inverter Step Response

- Ex: find step response of inverter driving load cap

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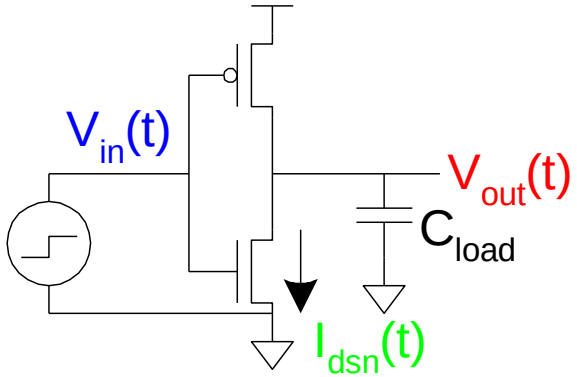
$$V_{out}(t < t_0) = V_{DD}$$

$$\frac{dV_{out}(t)}{dt} =$$



Inverter Step Response

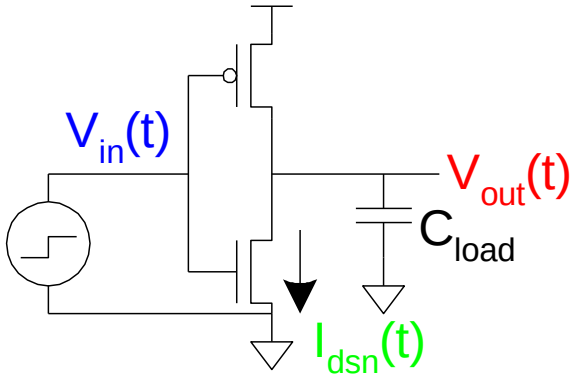
- Ex: find step response of inverter driving load cap

$$V_{in}(t) = u(t - t_0)V_{DD}$$

$$V_{out}(t < t_0) = V_{DD}$$

$$\frac{dV_{out}(t)}{dt} = -\frac{I_{dsn}(t)}{C_{load}}$$

$$I_{dsn}(t) = \begin{cases} t \le t_0 \\ V_{out} > V_{DD} - V_t \\ V_{out} < V_{DD} - V_t \end{cases}$$



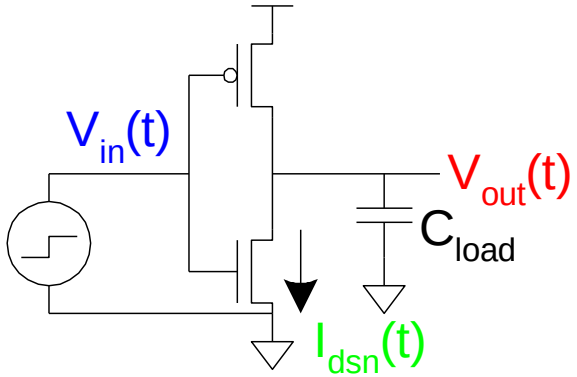
Inverter Step Response

- Ex: find step response of inverter driving load cap

$$V_{in}(t) = u(t - t_0)V_{DD}$$

$$V_{out}(t < t_0) = V_{DD}$$

$$\frac{dV_{out}(t)}{dt} = -\frac{I_{dsn}(t)}{C_{load}}$$



$$I_{dsn}(t) = \begin{cases} 0 & t \le t_0 \\ \frac{\beta}{2}(V_{DD} - V)^2 & V_{out} > V_{DD} - V_t \\ \beta\left(V_{DD} - V_t - V_{out}(t)/2\right)V_{out}(t) & V_{out} < V_{DD} - V_t \end{cases}$$

$$I(t) = \frac{dQ}{dt} = C\frac{dV}{dt}$$

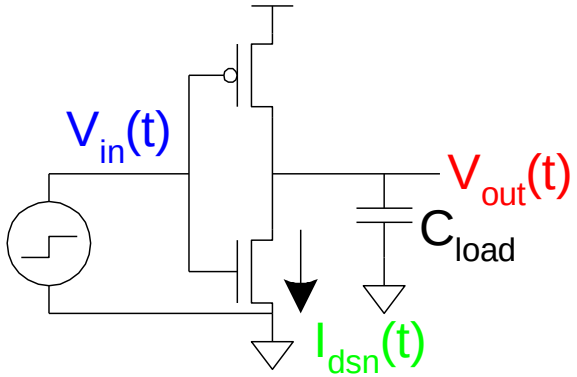
Inverter Step Response

- Ex: find step response of inverter driving load cap

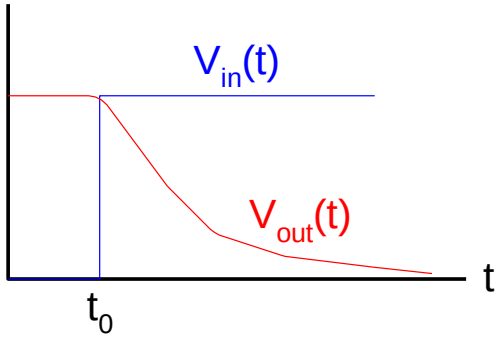
$$V_{in}(t) = u(t - t_0)V_{DD}$$

$$V_{out}(t < t_0) = V_{DD}$$

$$\frac{dV_{out}(t)}{dt} = -\frac{I_{dsn}(t)}{C_{load}}$$



$$I_{dsn}(t) = \begin{cases} 0 & t \le t_0 \\ \frac{\beta}{2}(V_{DD} - V)^2 & V_{out} > V_{DD} - V_t \\ \beta\left(V_{DD} - V_t - V_{out}(t)/2\right)V_{out}(t) & V_{out} < V_{DD} - V_t \end{cases}$$



Average Currents Method

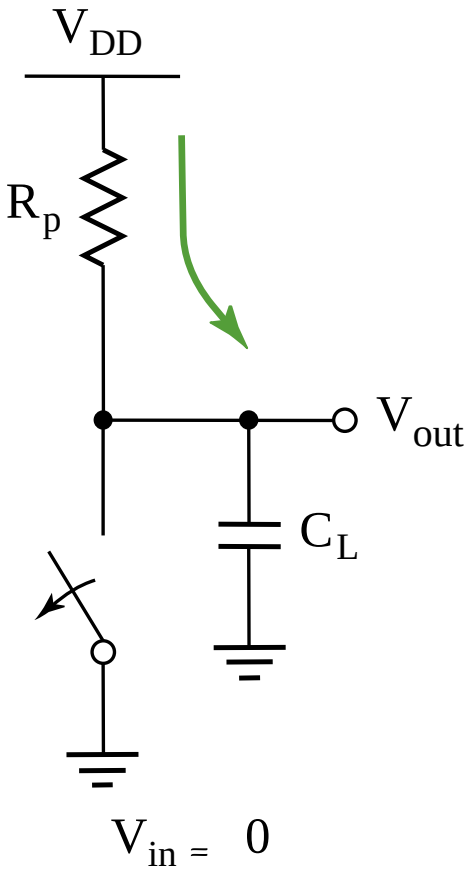
- Take the average of the current from the values at the extremes of the interval

$$t = \frac{C.\Delta V}{I_{avg}}$$

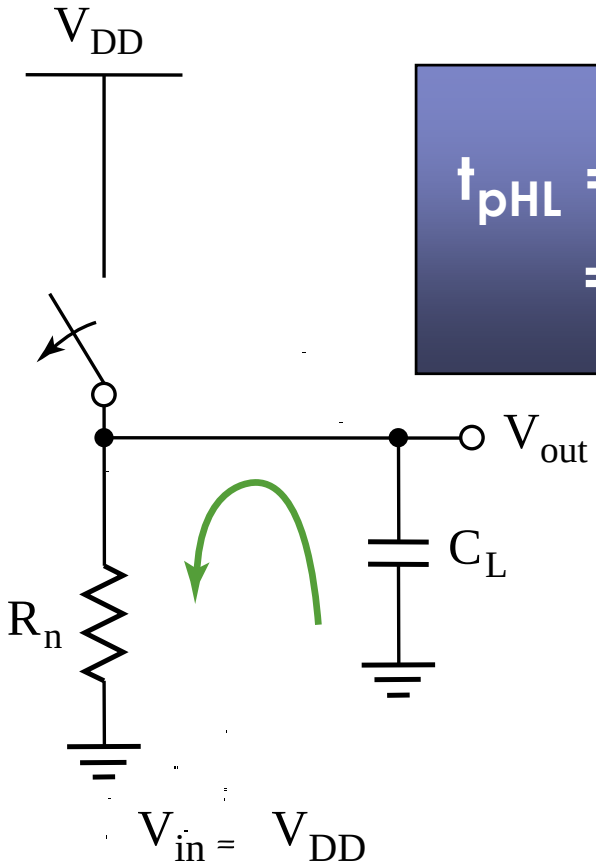
$$t_{PHL} = \frac{C_{load}.\Delta V_{HL}}{I_{avg,HL}} = \frac{C_{load}(V_{OH} - V_{50\%})}{\frac{I_{V=V_{OH}} + I_{V=V_{50\%}}}{2}}$$

$$t_{PLH} = \frac{C_{load}.\Delta V_{LH}}{I_{avg,LH}} = \frac{C_{load}(V_{50\%} - V_{OL})}{\frac{I_{V=V_{OL}} + I_{V=V_{50\%}}}{2}}$$

CMOS Inverter: Transient Response



(a) Low-to-high



(b) High-to-low

$$t_{pHL} = f(R_{on}.C_L) = 0.69\ R_{on}C_L$$

Pseudo-nMOS

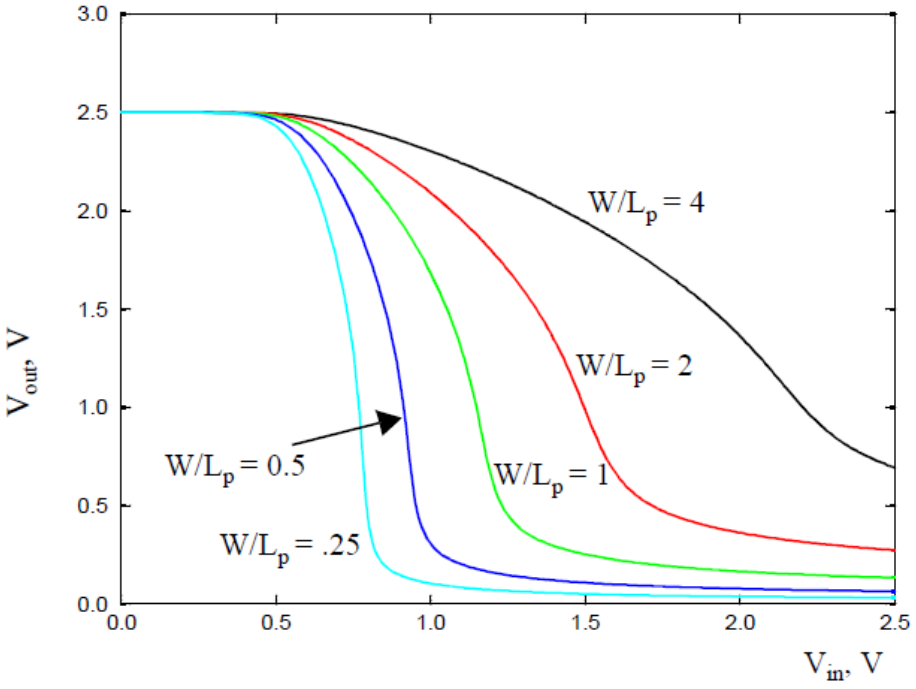


Figure 6.28 Voltage-transfer curves of the pseudo-NMOS inverter as a function of the PMOS size.